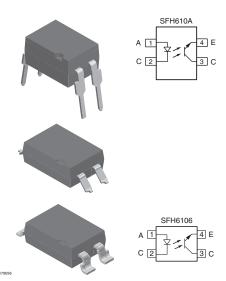


Vishay Semiconductors

# Optocoupler, Phototransistor Output, High Reliability, 5300 V<sub>RMS</sub>



#### **DESCRIPTION**

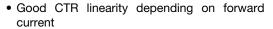
The SFH610A (DIP) and SFH6106 (SMD) feature a high current transfer ratio, low coupling capacitance and high isolation voltage. These couplers have a GaAs infrared diode emitter, which is optically coupled to a silicon planar phototransistor detector, and is incorporated in a plastic DIP-4 or SMD package.

The coupling devices are designed for signal transmission between two electrically separated circuits.

The couplers are end-stackable with 2.54 mm spacing.

Creepage and clearance distances of > 8.0 mm are achieved with option 6. This version complies with IEC 60950 (DIN VDE 0805) for reinforced insulation up to an operation voltage of 400  $V_{RMS}$  or DC. Specifications subject to change.

#### **FEATURES**





- Isolation test voltage, 5300 V<sub>RMS</sub>
- High collector emitter voltage, V<sub>CFO</sub> = 70 V
- Low saturation voltage
- · Fast switching times
- · Low CTR degradation
- Temperature stable
- Low coupling capacitance
- End stackable, 0.100" (2.54 mm) spacing
- High common mode interference immunity
- Lead (Pb)-free component
- Material categorization: For definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>

#### **AGENCY APPROVALS**

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-5 (VDE 0884) available with option 1
- CSA 93751
- BSI IEC 60950; IEC 60065

ORDERING INFORMATION	
PART	REMARKS
SFH610A-1	CTR 40 % to 80 %, DIP-4
SFH610A-2	CTR 63 % to 125 %, DIP-4
SFH610A-3	CTR 100 % to 200 %, DIP-4
SFH610A-4	CTR 160 % to 320 %, DIP-4
SFH610A-5	CTR 250 % to 500 %, DIP-4
SFH6106-1	CTR 40 % to 80 %, SMD-4
SFH6106-2	CTR 63 % to 125 %, SMD-4
SFH6106-3	CTR 100 % to 200 %, SMD-4
SFH6106-4	CTR 160 % to 320 %, SMD-4
SFH6106-5T	CTR 250 % to 500 %, SMD-4, tape and reel
SFH610A-1X006	CTR 40 % to 80 %, DIP-4 400 mil
SFH610A-1X018T	CTR 40 % to 80 %, SMD-4 400 mil, wide leadspread
SFH610A-2X006	CTR 63 % to 125 %, DIP-4 400 mil
SFH610A-3X006	CTR 100 % to 200 %, DIP-4 400 mil
SFH610A-3X007	CTR 100 % to 200 %, SMD-4
SFH610A-4X006	CTR 160 % to 320 %, DIP-4 400 mil

#### Note

For additional information on the available options refer to option information.



### Vishay Semiconductors

<b>ABSOLUTE MAXIMUM RAT</b>	<b>TINGS</b> ( $T_{amb} = 25  ^{\circ}C$ , unless oth	nerwise specifie	ed)	
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT	·			
Reverse voltage		V <sub>R</sub>	6	V
DC forward current		I <sub>F</sub>	60	mA
Surge forward current	t ≤ 10 μs	I <sub>FSM</sub>	2.5	Α
Power dissipation		P <sub>diss</sub>	100	mW
OUTPUT	·			
Collector emitter voltage		$V_{CE}$	70	V
Emitter collector voltage		$V_{EC}$	7	V
Collector current		I <sub>C</sub>	50	mA
Collector current	t <sub>p</sub> ≤ 1.0 ms	I <sub>C</sub>	100	mA
Power dissipation		P <sub>diss</sub>	150	mW
COUPLER	·			
Isolation test voltage between emitter and detector		$V_{ISO}$	5300	$V_{RMS}$
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Insulation thickness between emitter and detector			≥ 0.4	mm
Comparative tracking index per DIN IEC112/VDE 0303 part 1			≥ 175	
la eletion modistana e	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω
Isolation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C
Ambient temperature range		T <sub>amb</sub>	- 55 to + 100	°C
Soldering temperature (1)	max. 10 s, dip soldering distance to seating plane ≥ 1.5 mm	$T_{sld}$	260	°C

#### Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
  implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
  maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT		
INPUT									
Forward voltage	$I_F = 60 \text{ mA}$		V <sub>F</sub>		1.25	1.65	V		
Reverse current	V <sub>R</sub> = 6 V		I <sub>R</sub>		0.01	10	μA		
Capacitance	$V_R = 0 V, f = 1 MHz$		Co		13		pF		
Thermal resistance			R <sub>thja</sub>		750		K/W		
OUTPUT									
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}$		C <sub>CE</sub>		5.2		pF		
Thermal resistance			R <sub>thja</sub>		500		K/W		
		SFH610A-1	I <sub>CEO</sub>		2	50	nA		
		SFH6106-1	I <sub>CEO</sub>		2	50	nA		
		SFH610A-2	I <sub>CEO</sub>		2	50	nA		
		SFH6106-2	I <sub>CEO</sub>		2	50	nA		
Collector emitter leakage aurrent	V <sub>CE</sub> = 10 V	SFH610A-3	I <sub>CEO</sub>		5	100	nA		
Collector emitter leakage current	ACE = 10 A	SFH6106-3	I <sub>CEO</sub>		5	100	nA		
		SFH610A-4	I <sub>CEO</sub>		5	100	nA		
		SFH6106-4	I <sub>CEO</sub>		5	100	nA		
		SFH610A-5	I <sub>CEO</sub>		5	100	nA		
		SFH6106-5T	I <sub>CEO</sub>		5	100	nA		



# Vishay Semiconductors

ELECTRICAL CUADACTERISTICS (T									
ELECTRICAL CHARAC	<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER TEST CONDITION PART SYMBOL MIN. TYP. MAX. UN									
COUPLER	COUPLER								
Collector emitter saturation voltage	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 2.5 mA		V <sub>CEsat</sub>		0.25	0.4	V		
Coupling capacitance	f = 1 MHz		C <sub>C</sub>		0.4		pF		

#### Note

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering
evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER R	CURRENT TRANSFER RATIO								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT		
		SFH610A-1	CTR	40		80	%		
		SFH6106-1	CTR	40		80	%		
		SFH610A-2	CTR	63		125	%		
		SFH6106-2	CTR	63		125	%		
	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 5.0 V	SFH610A-3	CTR	100		200	%		
	IF = 10 IIIA, VCE = 3.0 V	SFH6106-3	CTR	100		200	%		
		SFH610A-4	CTR	160		320	%		
		SFH6106-4	CTR	160		320	%		
		SFH610A-5	CTR	250		500	%		
I <sub>C</sub> /I <sub>F</sub>		SFH6106-5T	CTR	250		500	%		
		SFH610A-1	CTR	13	30		%		
		SFH6106-1	CTR	13	30		%		
		SFH610A-2	CTR	22	45		%		
	$I_{\rm F} = 1  \text{mA},  V_{\rm CF} = 5  \text{V}$	SFH6106-2	CTR	22	45		%		
	IF = 1 IIIA, VCE = 5 V	SFH610A-3	CTR	34	70		%		
		SFH6106-3	CTR	34	70		%		
		SFH610A-4	CTR	56	90		%		
		SFH6106-4	CTR	56	90		%		

SWITCHING CHA	RACTERISTICS						
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
NON-SATURATED							
Current	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		I <sub>F</sub>		10		mA
Rise time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t <sub>r</sub>		2		μs
Fall time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t <sub>f</sub>		2		μs
Turn-on time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t <sub>on</sub>		3		μs
Turn-off time	$V_{CC} = 5 \text{ V}, R_L = 75 \Omega$		t <sub>off</sub>		2.3		μs
Cut-off frequency	V <sub>CC</sub> = 5 V		F <sub>CO</sub>		250		kHz
SATURATED							
		SFH610A-1			20		A
		SFH6106-1	· I <sub>F</sub>		20		mA
		SFH610A-2	_		10		A
Current		SFH6106-2	· I <sub>F</sub>				mA
Current		SFH610A-3	_		40		A
		SFH6106-3	· I <sub>F</sub>		10		mA
		SFH610A-4			-		A
		SFH6106-4	· I <sub>F</sub>		5		mA



# Vishay Semiconductors

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
SATURATED		l			l		
		SFH610A-1					μs
		SFH6106-1	t <sub>r</sub>		2		
		SFH610A-2					
B: "		SFH6106-2	t <sub>r</sub>		3		μs
Rise time		SFH610A-3					
		SFH6106-3	- t <sub>r</sub>		3		μs
		SFH610A-4			4		
		SFH6106-4	t <sub>r</sub>		4		μs
		SFH610A-1			11		
		SFH6106-1	- t <sub>f</sub>		''		μs
		SFH610A-2	+		14		μs
Fall time		SFH6106-2	t <sub>f</sub>				μs
Fall time		SFH610A-3	t <sub>f</sub>		14		110
		SFH6106-3					μs
		SFH610A-4			15		μs
		SFH6106-4					μδ
		SFH610A-1	t <sub>on</sub>		3		μs
		SFH6106-1	٠on				μδ
		SFH610A-2	t <sub>on</sub>		4.2		μs
Turn-on time		SFH6106-2	٠on				μδ
Turn on time		SFH610A-3	t <sub>on</sub>		4.2		μs
		SFH6106-3	con	ron			μο
		SFH610A-4	t <sub>on</sub>		6		μs
		SFH6106-4	con				μο
		SFH610A-1	t <sub>off</sub>		18		μs
Turn-off time		SFH6106-1	COII		10		μο
		SFH610A-2	t <sub>off</sub>		23		μs
		SFH6106-2	-011		20		μο
		SFH610A-3	t <sub>off</sub>		23		μs
		SFH6106-3	FOII		20		
		SFH610A-4	t <sub>off</sub>		25		μs
		SFH6106-4	Loff		25		μο

### Note

• All values presented are typical values.

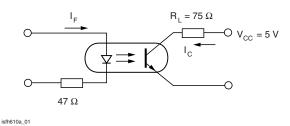


### Vishay Semiconductors

SAFETY AND INSULATIO RATINGS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Climatic classification (according to IEC 68 part 1)				55/100/21				
Comparative tracking index		CTI	175		399			
$V_{IOTM}$			10000			V		
V <sub>IORM</sub>			890			V		
P <sub>SO</sub>					400	mW		
I <sub>SI</sub>					275	mA		
T <sub>SI</sub>					175	°C		
Creepage distance	standard DIP-4		7			mm		
Clearance distance	standard DIP-4		7			mm		
Creepage distance	400 mil DIP-4		8			mm		
Clearance distance	400 mil DIP-4		8			mm		
Insulation thickness, reinforced rated	per IEC 60950 2.10.5.1		0.4			mm		

#### Note

### TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)



 $V_{CC} = 5 V$ 

isfh610a\_02

Fig. 1 - Linear Operation (without saturation)

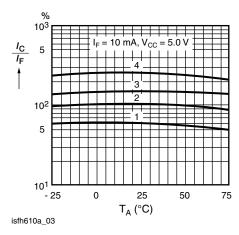
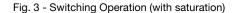


Fig. 2 - Current Transfer Ratio (CTR) vs. Temperature



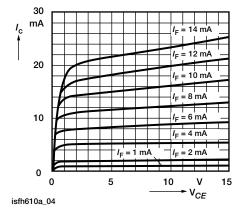


Fig. 4 - Output Characteristics (typ.) Collector Current vs. Collector Emitter Voltage

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with
the safety ratings shall be ensured by means of protective circuits.

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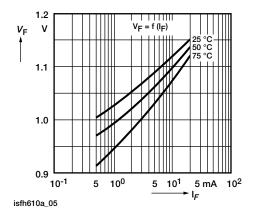


Fig. 5 - Diode Forward Voltage vs. Forward Current

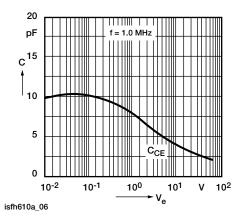


Fig. 6 - Transistor Capacitance (typ.) vs. Collector Emitter Voltage

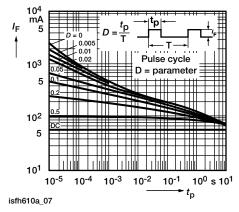


Fig. 7 - Permissible Pulse Handling Capability Forward Current vs. Pulse Width

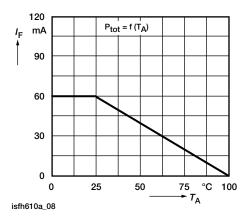


Fig. 8 - Permissible Power Dissipation vs. Temperature

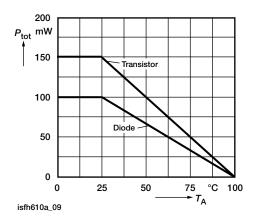


Fig. 9 - Permissible Diode Forward Current vs.
Ambient Temperature

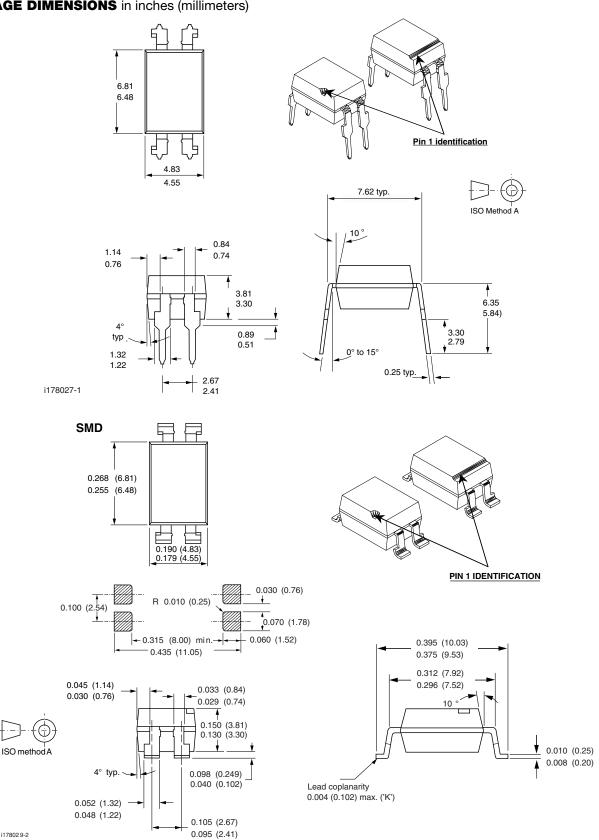


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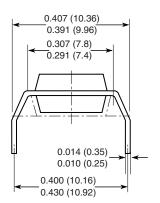
### PACKAGE DIMENSIONS in inches (millimeters)



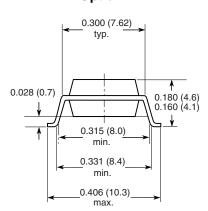


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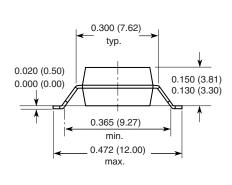
### Option 6



### Option 7



### **Option 8**





### **Legal Disclaimer Notice**

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000